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## 1/f Noise in Platinum Films and Ultrathin Platinum Wires: Evidence for a Common, Bulk Origin

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The 1/f noise of platinum films and ultrathin platinum wires has been found to scale inversely with the number of atoms in the sample,  $N$ , for  $N$  in the range  $10^7$  to  $10^{14}$ . This strongly reinforces the idea that the 1/f noise of continuous metal films is of bulk origin, and demonstrates that the dominant form of excess low-frequency noise in the very small structures investigated here is the bulk 1/f noise.

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Recently there has been much interest in the physics of very small structures. Progress in the fabrication of these structures has contributed greatly to the understanding of a wide variety of phenomena.<sup>1</sup> For example, the study of ultrathin wires ( $d \lesssim 500 \text{ \AA}$ , where  $d$  is the diameter) has provided new insight into the effects of impurities on electrical conduction in metals.<sup>2,3</sup> Another potentially fruitful area of research involving very small structures is the study of fluctuation processes. In most cases, the relative magnitude of a fluctuation is inversely proportional to the volume of the system,<sup>4</sup> so that one might expect that previously unobservable fluctuations could be extremely important in very small struc-

tures. One type of fluctuation whose effects may be readily measured is the electrical noise of a resistor. If the voltage across a resistor is sampled as a function of time, the noise-power spectral density,  $S_v(f)$ , may be obtained. When there is no current flow, we expect  $S_v = 4kTR$ , which is the well-known Johnson (Nyquist) noise.<sup>5</sup> When a direct current is passed through the resistor, however, noise in excess of the Johnson noise is commonly observed. The excess noise-power spectral density is often found to be proportional to  $1/f^\alpha$ , with  $\alpha \approx 1$ , and it is therefore referred to as "1/f noise." Although 1/f noise has been investigated extensively in recent years, its origin is not known.<sup>6,7</sup> Indeed, it is not yet

even clear whether the  $1/f$  noise of semiconductors is a surface effect, a bulk effect, or some combination of the two.<sup>6,8,9</sup> For metals, on the other hand, the general intuition is that the  $1/f$  noise is of bulk origin.<sup>6,7</sup> However, there is actually very little experimental evidence to directly substantiate such an assertion, and what evidence there is remains somewhat open to interpretation.<sup>10,11</sup> This uncertainty is due to the limited range of sample sizes in which the noise has been studied previously<sup>10,12,13</sup> and to the large sample-to-sample variations of the noise magnitude which are commonly reported, even in nominally identical samples.<sup>10,12-14</sup> We have investigated the low-frequency excess noise of platinum films ( $10^{11} < N < 10^{14}$ , where  $N$  is the number of atoms in the sample) which were prepared similarly to the metal films studied by previous workers,<sup>12,13</sup> and of ultrathin platinum wires ( $10^7 < N < 10^{11}$ ) which were prepared lithographically.<sup>3,15-17</sup> We find that the dominant form of excess noise for both the films and wires is  $1/f$  noise, and that the noise magnitude is inversely proportional to  $N$  over the entire range of samples studied. This strongly suggests that the dominant low-frequency fluctuation process in the wires is the same as that which causes the bulk  $1/f$  noise in platinum.

The platinum films were deposited by ion-beam sputtering onto glass and sapphire substrates, and ranged in thickness from 80 to 200 Å. The films were cut with a tungsten needle to form strips 50–700 μm long and 10–70 μm wide. Electrical contact to the films was made with indium-tin solder and/or evaporated gold contact pads. Using the technique of “step-edge lithography,” which is described in detail elsewhere,<sup>3,15-17</sup> we fabricated platinum wires of lengths 0.3–250 μm and cross-sectional areas of  $2.3 \times 10^{-12}$ – $3.9 \times 10^{-11}$  cm<sup>2</sup> ( $150 \text{ Å} < d < 650 \text{ Å}$ ) on glass substrates. Since these wires are made starting from sputtered platinum films, they are essentially films which are much thinner and narrower than they are long.<sup>3,15-17</sup> We use the term “wire” to emphasize the very different length-to-width ratios of the two different types of samples. Electrical contact to the wires was made with platinum films in conjunction with silver paint and indium-tin solder pads.<sup>3</sup> Both the films and the wires had resistivities,  $\rho$ , in the range 40–60 μΩ cm,<sup>18</sup> and temperature coefficients of resistivity  $[(1/\rho)(d\rho/dT)]$  of  $(5-7) \times 10^{-4} \text{ K}^{-1}$ . Transmission electron microscope studies showed that the grain size of the platinum was  $\leq 75 \text{ Å}$  with any

holes  $< 10 \text{ Å}$ ; hence, the samples studied here were continuous.<sup>19</sup>

Noise measurements were performed at room temperature; the apparatus used was the same as that described elsewhere.<sup>20</sup> In all cases the excess noise,  $S_v(f)$ , was proportional to  $1/f^\alpha$  with  $\alpha \approx 1.15$ , over the frequency range measured ( $0.2 < f < 100 \text{ Hz}$ ), which is characteristic of “ $1/f$ ” noise. For the platinum films we have studied ( $100 \text{ Ω} < R < 500 \text{ Ω}$ ), and in previous studies<sup>10,12,13</sup> of the  $1/f$  noise in metal films ( $1.0 \text{ Ω} \leq R \leq 1.0 \text{ kΩ}$ ), it was not possible to perform measurements of the noise power below about 0.1 Hz. This is due to the impaired low-frequency response of available amplifiers and/or the high level of the amplifier noise. However, because of the relatively high impedance of the wires we have studied ( $8.0 \text{ kΩ} \leq R \leq 140 \text{ kΩ}$ ), it was possible to extend the measurements to considerably lower frequencies. The results for a typical wire are shown in Fig. 1, where the noise-power spectral density is plotted as a function of frequency. The noise power is seen to be proportional to  $1/f^{1.15}$  over the entire frequency range. Thus, any characteristic time scale of the fluctuation process must lie outside the range implied by the high- and low-frequency limits in

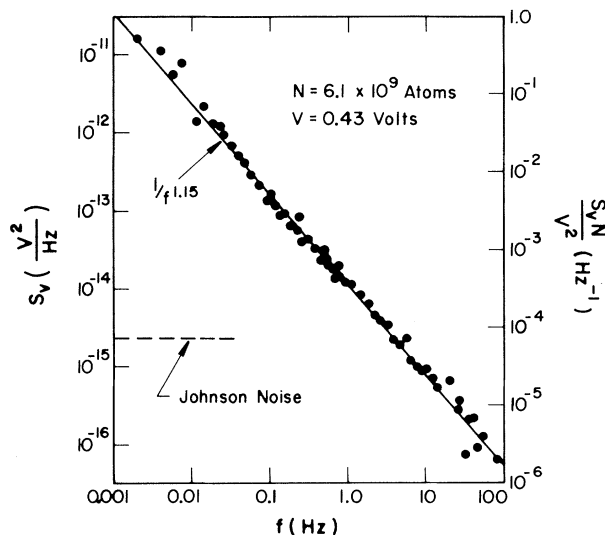


FIG. 1.  $S_v$  as a function of  $f$  for a platinum wire. The solid line is proportional to  $1/f^{1.15}$ , and the dashed line indicates the Johnson-noise level (although the Johnson noise has been subtracted in order to obtain the excess noise). The normalized noise power,  $SN/V^2$ , is given on the right-hand scale.

Fig. 1; i.e., it must be less than 0.01 s or greater than 500 s. We should remark that the overall noise magnitude of this wire is described fairly well by the semiempirical formula developed by Hooge and co-workers<sup>6,21</sup>:

$$S_v(f) = (\mu/\mu_{ph})^2 \gamma V^2 / N_c f. \quad (1)$$

Here  $\mu$  is the total mobility,  $\mu_{ph}$  is the mobility due to electron-phonon scattering,  $N_c$  is the number of free carriers<sup>22</sup> in the sample, and  $\gamma \approx 2 \times 10^{-3}$ . For this sample  $\mu/\mu_{ph} \approx \frac{1}{4}$ , and so (1) predicts that  $S_v(10 \text{ Hz}) \approx 4 \times 10^{-16} \text{ V}^2/\text{Hz}$ , while we find  $S_v(10 \text{ Hz}) \approx 8 \times 10^{-16} \text{ V}^2/\text{Hz}$ . Since the value of  $N$  has an experimental uncertainty of nearly a factor of 2, the agreement is satisfactory. However, in work which is reported elsewhere,<sup>14</sup> we have shown that (1) does not provide an accurate description of the mobility dependence of the  $1/f$  noise in metals. Thus, the agreement with the prediction of (1) appears to be fortuitous.

In Fig. 2 we show the "normalized" noise power ( $S_v f / V^2$ ) as a function of the number of atoms in the sample,  $N$ , for a number of films and wires. Normalizing the noise power in this way removes the effect of the different measuring currents used (since for each sample it was found that  $S_v$

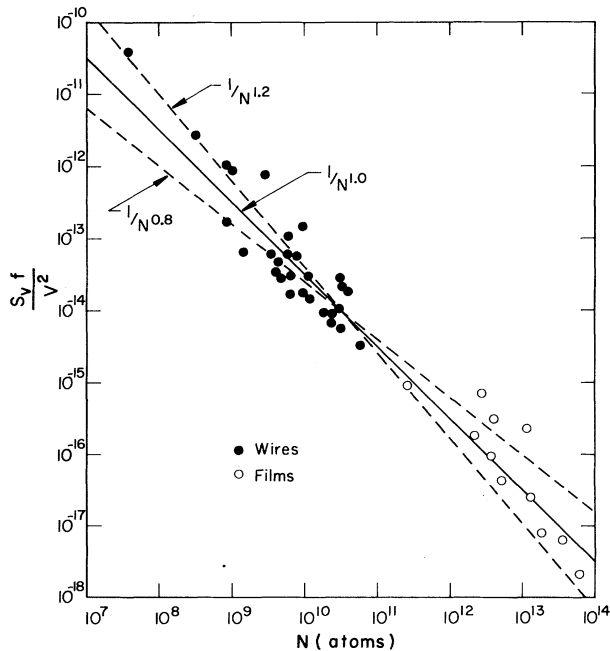


FIG. 2.  $S_v f / V^2$  at  $f = 10 \text{ Hz}$  as a function of  $N$  for platinum films and wires. The solid line is proportional to  $1/N^{1.0}$ . The dashed lines are proportional to  $1/N^{1.2}$ , and to  $1/N^{0.8}$ , as discussed in the text.

$\sim I^\beta \sim V^\beta$ , with  $\beta = 2.0 \pm 0.1$ , as expected<sup>6,7</sup>), and allows a direct comparison of the noise levels of different samples.<sup>10,13,14</sup> If the noise in the wires and films is due to a purely bulk fluctuation, one would expect the normalized noise power to be proportional to  $1/N$ . It can be seen from Fig. 2 that our results are quite consistent with this prediction. To give a feeling for the uncertainties involved, Fig. 2 also shows lines proportional to  $1/N^{0.8}$  and  $1/N^{1.2}$ . It can be seen that our results are not really consistent with either of these, and we therefore conclude that the normalized noise power is proportional to  $1/N^\delta$ , with  $\delta = 1.0 \pm 0.2$ . This implies that the noise of the films and wires has a common cause. If the noise of the wires were caused by a different mechanism than the noise of the films (as one might have easily imagined since the wires are of much smaller volume, and have a typically threefold greater surface-to-volume ratio, than the films), then there should be some change in scaling between the noise of the wires and the films.<sup>23</sup> Clearly, there is no such change<sup>14,24</sup> to within the  $\approx 20\%$  uncertainty due to the "scatter." Further, the "fully" normalized noise power ( $S_v N f / V^2$ ) was found not to depend upon any of the measured parameters<sup>25</sup>; in particular, it did not depend upon the cross-sectional area of the sample. This strongly suggests that, while surface effects (or other "nonintrinsic" sources of noise) may contribute to the sample-to-sample variations of the noise,  $1/f$  noise of bulk origin is the dominant source of excess noise in both the films and the wires. It is interesting to note that the persistence of the  $1/N$  dependence to the smallest wires fabricated implies<sup>26</sup> that (at least for platinum) any characteristic length scale of the fluctuation process is  $\approx 3000 \text{ \AA}$  along the direction of current flow, and  $\approx 150 \text{ \AA}$  in both transverse dimensions.

In summary, we find that the dominant source of low-frequency excess noise in platinum films and ultrathin platinum wires is  $1/f$  noise. The noise scales inversely with the number of atoms,  $N$ , in the sample for more than six orders of magnitude variation in  $N$ , which is compelling evidence that the  $1/f$  noise of both the films and the wires is of bulk origin.

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<sup>18</sup>The resistivity was nearly four times the bulk value, due to the increased impurity scattering commonly found in sputtered films. Some boundary scattering was also evident in the thinner ( $t < 150$  Å) films.

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<sup>23</sup>We should remark that the noise of a few of the films was initially 1–2 orders of magnitude above the level of (1). With aging, the noise decreased in magnitude and stabilized at a level near that of (1). We do not know the reason for this behavior; however, *none* of the wires exhibited such an effect.

<sup>24</sup>It is noted in Ref. 14 that the best measure of the noise in metal films seem to be the “minimum” noise shown. There is a well-defined minimum level of  $1/f$  noise for platinum, which is evident in Fig. 2. The minimum noise scales almost exactly as  $1/N$ , and is in good agreement with the results reported in Ref. 14. Thus, while there is about a factor of 10 “scatter” from sample to sample, the minimum noise scales continuously with  $N$  at the transition between the films and wires. This indicates that the noise is independent of the specific sample geometry.

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